



## Voidless-Hermetically-Sealed Unidirectional 150 W Low-Capacitance Transient Voltage Suppressors

### DESCRIPTION

This series of voidless-hermetically-sealed unidirectional low-capacitance Transient Voltage Suppressor (TVS) designs are ideal for protecting higher frequency applications in high-reliability applications where a failure cannot be tolerated. They include a unique rectifier diode in series and opposite direction from the TVS to achieve a very low capacitance of 4 pF. This product series provides a working peak “standoff” voltage selection from 6.8 to 170 volts with 150 watt ratings. They are very robust in hard-glass construction and also use an internal metallurgical bond identified as Category 1 for high reliability applications. These devices are also available in axial leaded packages for thru-hole mounting.

**Important:** For the latest information, visit our website <http://www.microsemi.com>.

### FEATURES

- High surge current and peak pulse power unidirectional protection for sensitive circuits.
- Very low capacitance for high frequency or high baud rate applications.
- Bidirectional capability with two devices in anti-parallel (see Figure 5).
- Triple-layer passivation.
- Internal “Category 1” metallurgical bonds.
- Voidless hermetically sealed glass package.
- RoHS compliant versions are available.

### APPLICATIONS / BENEFITS

- High reliability transient protection.
- Extremely robust construction.
- Working peak “standoff” voltage ( $V_{WM}$ ) from 6.8 to 170 volts.
- Available as 150 W peak pulse power ( $P_{PP}$ ) at 10/1000  $\mu$ s.
- Lowest available capacitance for 150 W rated TVS.
- ESD and EFT protection per IEC61000-4-2 and IEC61000-4-4 respectively.
- Secondary lightning protection per select levels in IEC61000-4-5.
- Flexible axial-leaded mounting terminals.
- Nonsensitive to ESD per MIL-STD-750 method 1020.
- Inherently radiation hard as described in Microsemi [MicroNote 050](#).

### MAXIMUM RATINGS

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	$T_J$ and $T_{STG}$	-55 to +175	$^{\circ}C$
Capacitance at zero volts	C	4	pF
Thermal Resistance junction to ambient	$R_{\theta JA}$	150	$^{\circ}C/W$
Peak Pulse Power at 25 $^{\circ}C$ (10 $\mu$ s/1000 $\mu$ s)	$P_{PP}$	150	W
Impulse repetition rate (duty factor)	d.f	0.01	%
Steady State (Average) Power @ $T_A = 25^{\circ}C$	$P_{M(AV)}$	1.0	W
Solder Temperature (10 s maximum)		260	$^{\circ}C$


**Note:** Steady-state power ratings with reference to ambient are for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled where  $T_{J(MAX)}$  is not exceeded.



“A” Package

Also available in:

“A” MELF package  
(surface mount)

 1N8149US – 1N8182US

#### MSC – Lawrence

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Lawrence, MA 01841  
1-800-446-1158  
(978) 620-2600  
Fax: (978) 689-0803

#### MSC – Ireland

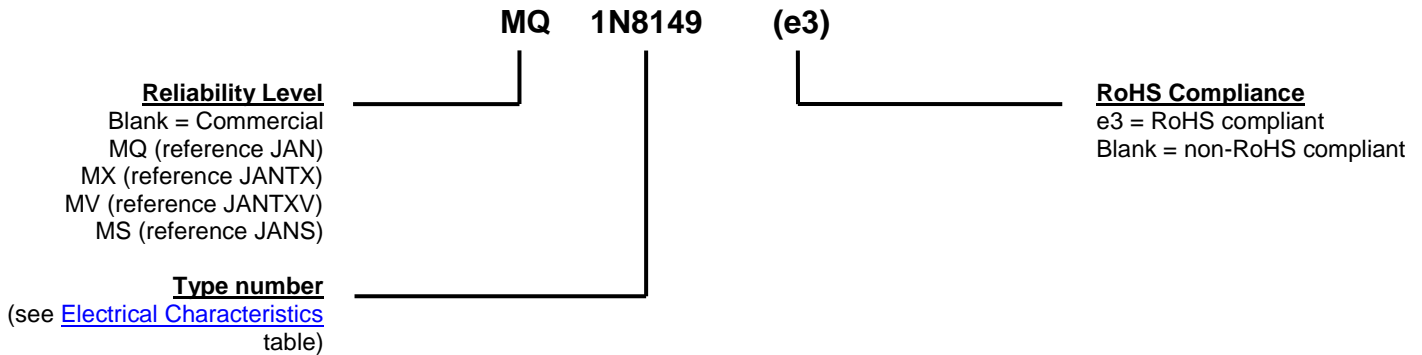
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[www.microsemi.com](http://www.microsemi.com)

**MECHANICAL and PACKAGING**

- CASE: Hermetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: Axial-leads are tin/lead or RoHS compliant matte/tin plating over copper.
- MARKING: Body paint and part number
- POLARITY: Cathode band
- MOUNTING: Any position
- TAPE & REEL option: Standard per EIA-296.
- WEIGHT: Approximately 340 milligrams.
- See [Package Dimensions](#) on last page.

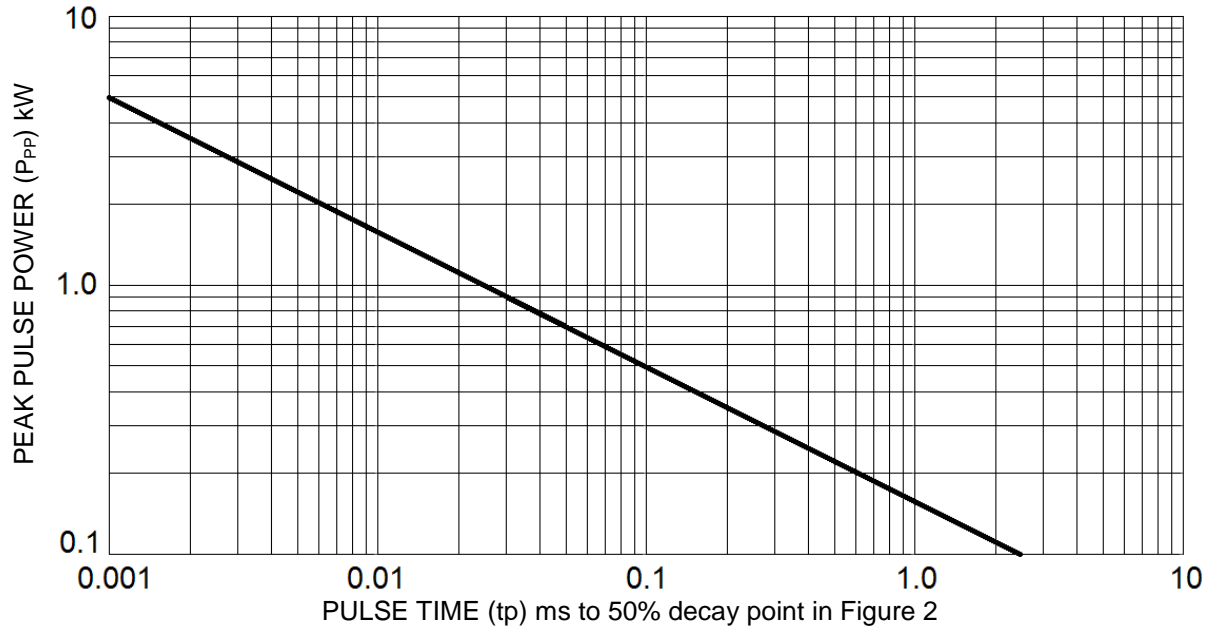
**PART NOMENCLATURE**

**SYMBOLS & DEFINITIONS**

Symbol	Definition
$\alpha_{V(BR)}$	Temperature Coefficient of Breakdown Voltage: The change in breakdown voltage divided by the change in temperature that caused it expressed in %/°C or mV/°C.
$V_{(BR)}$	Breakdown Voltage: The voltage across the device at a specified current $I_{(BR)}$ in the breakdown region.
$V_{WM}$	Working Standoff Voltage: The maximum-rated value of dc or repetitive peak positive cathode-to-anode voltage that may be continuously applied over the standard operating temperature.
$I_D$	Standby Current: The current through the device at rated stand-off voltage.
$I_{(BR)}$	Breakdown Current: The current used for measuring Breakdown Voltage $V_{(BR)}$
$I_{PP}$	Peak Impulse Current: The maximum rated random recurring peak impulse current or nonrepetitive peak impulse current that may be applied to a device. A random recurring or nonrepetitive transient current is usually due to an external cause, and it is assumed that its effect will have completely disappeared before the next transient arrives.
$V_C$	Clamping Voltage: The voltage across the device in a region of low differential resistance during the application of an impulse current ( $I_{PP}$ ) for a specified waveform.
$P_{PP}$	Peak Pulse Power. The rated random recurring peak impulse power or rated nonrepetitive peak impulse power. The impulse power is the maximum-rated value of the product of $I_{PP}$ and $V_C$ .
$C_T$	Total Capacitance: The total small signal capacitance between the diode terminals of a complete device.
$V_{WIB}$	Inverse Blocking Voltage: The maximum-rated value of dc or peak blocking voltage in the inverse direction.
$I_{IB}$	Blocking Leakage Current: The current through the device at the rated inverse blocking voltage ( $V_{WIB}$ ).

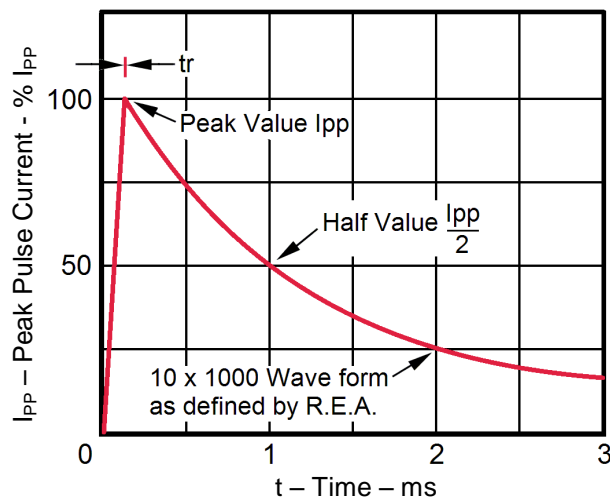
ELECTRICAL CHARACTERISTICS @ T<sub>A</sub> = 25°C unless otherwise noted.

Type Number	Minimum Breakdown Voltage (V <sub>BR</sub> )	Breakdown Current (I <sub>BR</sub> )	Working Standoff Voltage (V <sub>WM</sub> )	Maximum Standby Current (I <sub>D</sub> )	Maximum Peak Clamping Voltage (V <sub>C</sub> )	Maximum Surge Current (I <sub>PP</sub> )	Maximum V <sub>BR</sub> Temperature Coefficient (α <sub>V(BR)</sub> )	Capacitance (C <sub>T</sub> )	Inverse Blocking Voltage (V <sub>WIB</sub> )	Blocking Leakage Current (I <sub>IB</sub> )
	V	mA	V	μA	V	A	%/°C	pF	V	μA
1N8149	7.79	10	6.8	20	12.8	11.7	.065	4	300	1
1N8150	8.65	1	7.5	10	13.5	11.1	.068	4	300	1
1N8151	9.50	1	8.5	10	14.5	10.3	.073	4	300	1
1N8152	10.4	1	9.0	5	15.6	9.62	.075	4	300	1
1N8153	11.4	1	10.0	1	16.9	8.88	.078	4	300	1
1N8154	12.4	1	11.0	1	18.2	8.24	.081	4	300	1
1N8155	13.8	1	12.0	1	20.2	7.42	.084	4	300	1
1N8156	15.2	1	13.0	1	22.3	6.73	.086	4	300	1
1N8157	17.1	1	15.0	1	25.1	5.98	.088	4	300	1
1N8158	19.0	1	17.0	0.5	27.7	5.42	.090	4	300	1
1N8159	20.9	1	18.0	0.5	30.5	4.92	.092	4	300	1
1N8160	22.8	1	20.0	0.5	33.3	4.50	.094	4	300	1
1N8161	25.7	1	22.0	0.5	37.4	4.01	.096	4	300	1
1N8162	28.5	1	25.0	0.5	41.6	3.60	.097	4	300	1
1N8163	31.4	1	28.0	0.5	45.7	3.28	.098	4	300	1
1N8164	34.2	1	30.0	0.5	49.9	3.01	.099	4	300	1
1N8165	37.1	1	33.0	0.5	53.6	2.80	.100	4	300	1
1N8166	40.9	1	36.0	0.5	59.1	2.54	.101	4	300	1
1N8167	44.7	1	40.0	0.5	64.6	2.32	.101	4	300	1
1N8168	48.5	1	43.0	0.5	70.1	2.14	.102	4	300	1
1N8169	53.2	1	47.0	0.5	77.0	1.95	.103	4	300	1
1N8170	58.9	1	53.0	0.5	85.3	1.76	.104	4	300	1
1N8171	64.6	1	58.0	0.5	93.7	1.60	.104	4	300	1
1N8172	71.3	1	64.0	0.5	103.0	1.45	.105	4	300	1
1N8173	77.9	1	70.0	0.5	113.0	1.32	.105	4	300	1
1N8174	86.5	1	75.0	0.5	125.0	1.20	.105	4	300	1
1N8175	95.0	1	82.0	0.5	137.0	1.09	.106	4	300	1
1N8176	104.0	1	94.0	0.5	152.0	0.98	.107	4	300	1
1N8177	114.0	1	100.0	0.5	168.0	0.89	.107	4	300	1
1N8178	124.0	1	110.0	0.5	183.0	0.82	.107	4	300	1
1N8179	138.0	1	120.0	0.5	208.0	0.72	.108	4	300	1
1N8180	152.0	1	130.0	0.5	225.0	0.67	.108	4	300	1
1N8181	171.0	1	150.0	0.5	261.0	0.57	.108	4	300	1
1N8182	190.0	1	170.0	0.5	294.0	0.51	.108	4	300	1

GRAPHS

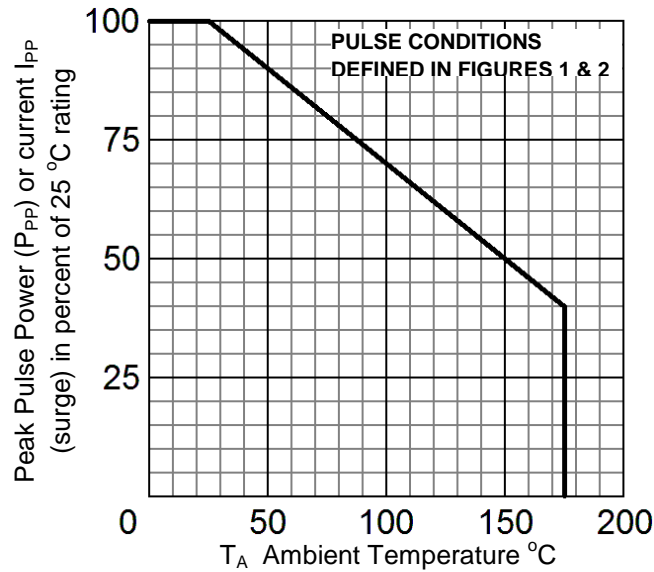


**FIGURE 1**  
PEAK PULSE POWER VS. PULSE TIME



**FIGURE 2**  
10/1000µs CURRENT IMPULSE WAVEFORM

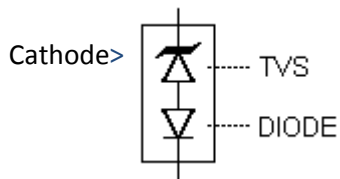
**GRAPHS**



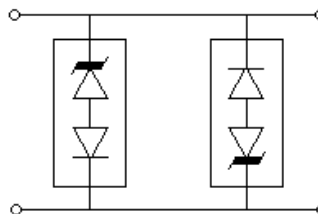
**FIGURE 3**  
DERATING CURVE

**SCHEMATIC APPLICATIONS**

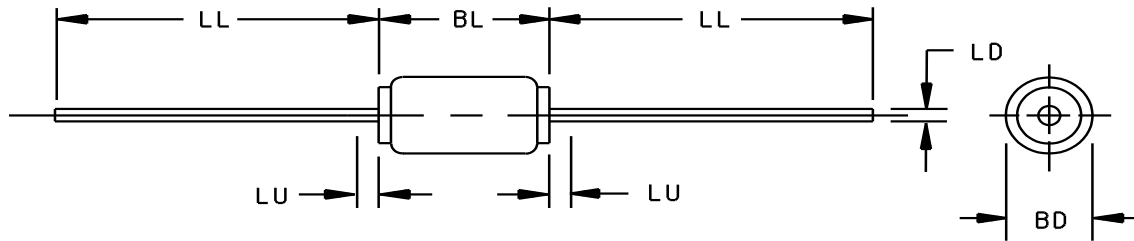
The TVS low capacitance device configuration described in this data sheet is shown in Figure 4 involving a TVS and a unique diode in series and opposite direction. For bidirectional low capacitance TVS applications, use two (2) low capacitance TVS devices as described in this data sheet in anti-parallel as shown in Figure 5. This will result in twice the capacitance of Figure 4 specified in this data sheet.



**FIGURE 4**  
Low Capacitance TVS



**FIGURE 5**  
Bidirectional configuration  
(2 Low Capacitance TVS  
devices in anti-parallel)

**PACKAGE DIMENSIONS**

**NOTES:**

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimension  $BD$  shall be measured at the largest diameter.
4. Dimension  $LU$  lead diameter uncontrolled in this area.
5. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi x$  symbology.

Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
<b>BD</b>	0.060	0.085	1.52	2.16	3
<b>BL</b>	0.106	0.175	2.69	4.45	
<b>LD</b>	0.028	0.032	0.71	0.81	
<b>LL</b>	0.800	1.300	20.32	33.02	
<b>LU</b>		0.050		1.27	4